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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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C mplete if Known

Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Art Unit	2842 2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608.

Sheet

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of

8

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
TUP	AA	5,761,115	06/02/1998	Kozicki et al.	
TUP	AB	6,084,796	07/04/2000	Kozicki et al.	
TUP	AC	5,914,893	06/22/1999	Kozicki et al.	
TUP	AD	5,896,312	04/20/1999	Kozicki et al.	
TUP	AE	6,388,324	05/14/2002	Kozicki et al.	
TUP	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
TUP	AG	5,500,532	03/19/1996	Kozicki et al.	
TUP	AH	6,418,049	07/09/2002	Kozicki et al.	
TUP	AI	5,751,012	05/12/1998	Wolstenholme et al.	
TUP	AJ	5,789,277	08/04/1998	Zahorik et al.	
TUP	AK	6,348,365	02/19/2202	Moore et al.	
	AL				
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	AN				
	AO				

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
TUP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
TUP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
TUP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
TUP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	<i>John T. Moore</i>	Date Considered	3/20/03
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Sheet 2 of 8

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Tup	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
Tup	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
Tup	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
Tup	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.	
Tup	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.	
Tup	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
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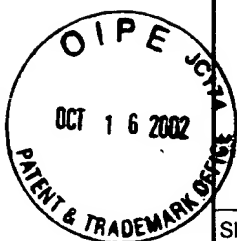
Sheet	3	of	8	Attorney Docket Number	M4065.0608/P608
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Group Art Unit	2812 2823
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		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
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Sheet	4	of	8
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Twp		silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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TUP	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	
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TUP	CX2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.	
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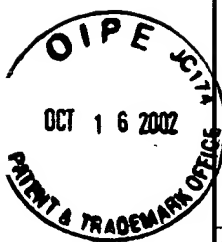
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/988,984
		Filing Date	November 19, 2001
		First Named Inventor	John T. Moore
		Group Art Unit	2012 28 23
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	M4065.0608/P608
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Sheet	8	of	8	Attorney Docket Number	M4065.0608/P608
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Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2842-2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

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Examiner Signature	<i>Phan Thanh</i>	Date Considered	3/20/02
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				Application Number	09/988,984
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				Art Unit	2842-2823
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0608/P608

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JP	AA	US 2002/0168820	11-14-2002	Kozicki, et al.	
JP	AB	6,469,364	10-22-2002	Kozicki	
	AC				
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